

74HC191

Presettable synchronous 4-bit binary up/down counter

Rev. 3 — 3 January 2017

Product data sheet

1. General description

The 74HC191 is an asynchronously presettable 4-bit binary up/down counter. It contains four master/slave flip-flops with internal gating and steering logic to provide asynchronous preset and synchronous count-up and count-down operation. Asynchronous parallel load capability permits the counter to be preset to any desired value. Information present on the parallel data inputs (D0 to D3) is loaded into the counter and appears on the outputs when the parallel load (\overline{PL}) input is LOW. This operation overrides the counting function. Counting is inhibited by a HIGH level on the count enable (\overline{CE}) input. When \overline{CE} is LOW internal state changes are initiated synchronously by the LOW-to-HIGH transition of the clock input. The up/down ($\overline{U/D}$) input signal determines the direction of counting as indicated in the function table. The \overline{CE} input may go LOW when the clock is in either state, however, the LOW-to-HIGH \overline{CE} transition must occur only when the clock is HIGH. Also, the $\overline{U/D}$ input should be changed only when either \overline{CE} or CP is HIGH. Overflow/underflow indications are provided by two types of outputs, the terminal count (TC) and ripple clock (RC). The TC output is normally LOW and goes HIGH when a circuit reaches zero in the count-down mode or reaches '15' in the count-up-mode. The TC output will remain HIGH until a state change occurs, either by counting or presetting, or until $\overline{U/D}$ is changed. Do not use the TC output as a clock signal because it is subject to decoding spikes. The TC signal is used internally to enable the \overline{RC} output. When TC is HIGH and \overline{CE} is LOW, the \overline{RC} output follows the clock pulse (CP). This feature simplifies the design of multistage counters as shown in [Figure 5](#) and [Figure 6](#). In [Figure 5](#), each \overline{RC} output is used as the clock input to the next higher stage. It is only necessary to inhibit the first stage to prevent counting in all stages, since a HIGH on \overline{CE} inhibits the \overline{RC} output pulse. The timing skew between state changes in the first and last stages is represented by the cumulative delay of the clock as it ripples through the preceding stages. This can be a disadvantage of this configuration in some applications. [Figure 6](#) shows a method of causing state changes to occur simultaneously in all stages. The \overline{RC} outputs propagate the carry/borrow signals in ripple fashion and all clock inputs are driven in parallel. In this configuration the duration of the clock LOW state must be long enough to allow the negative-going edge of the carry/borrow signal to ripple through to the last stage before the clock goes HIGH. Since the \overline{RC} output of any package goes HIGH shortly after its CP input goes HIGH there is no such restriction on the HIGH-state duration of the clock. In [Figure 7](#), the configuration shown avoids ripple delays and their associated restrictions. Combining the TC signals from all the preceding stages forms the \overline{CE} input for a given stage. An enable must be included in each carry gate in order to inhibit counting. The TC output of a given stage is not affected by its own \overline{CE} signal therefore the simple inhibit scheme of [Figure 5](#) and [Figure 6](#) does not apply. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .



2. Features and benefits

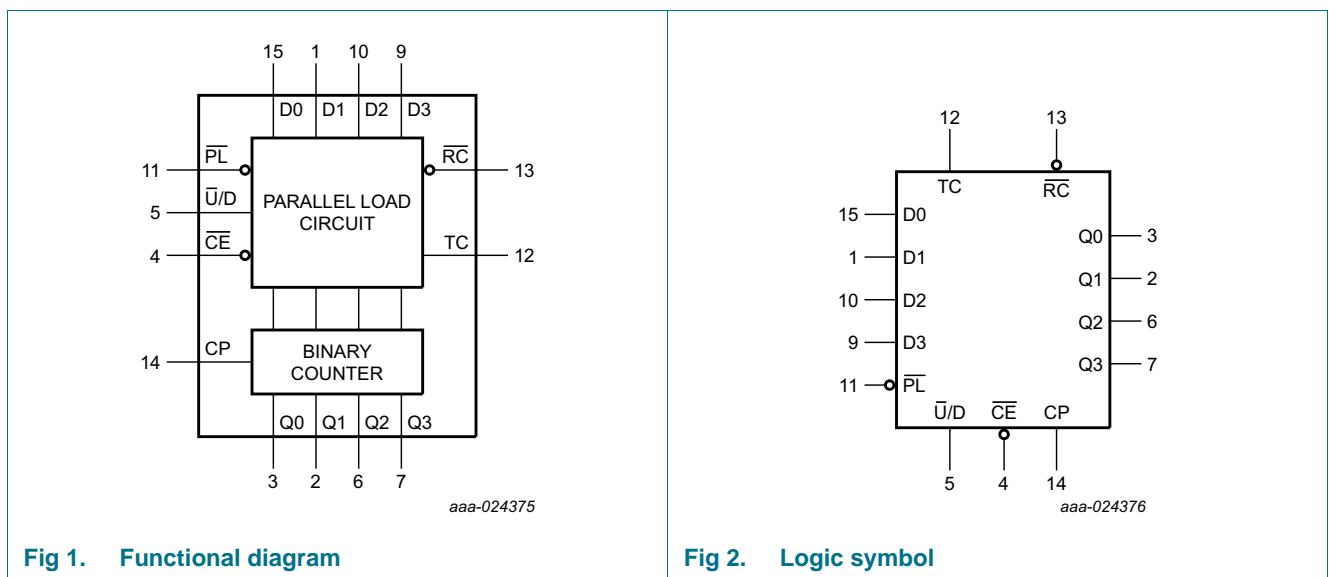
- Complies with JEDEC standard no. 7A
- Input levels:
 - ◆ For 74HC191: CMOS level
- Synchronous reversible counting
- Asynchronous parallel load
- Count enable control for synchronous expansion
- Single up/down control input
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

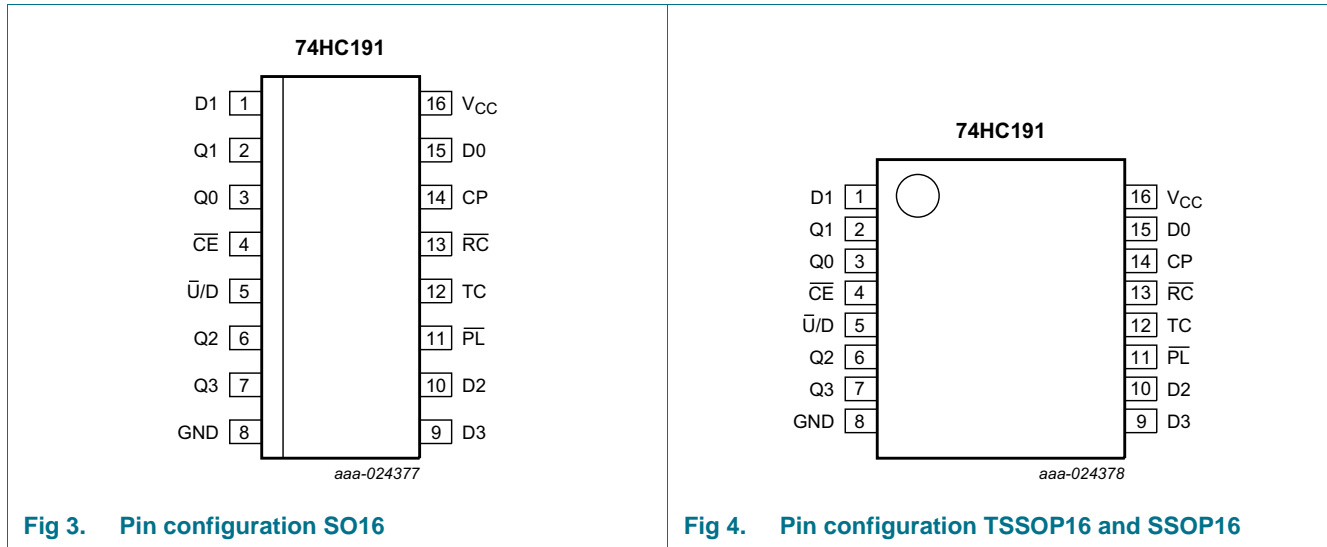
Type number	Package			Version
	Temperature range	Name	Description	
74HC191D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC191DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HC191PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
D0, D1, D2, D3	15, 1, 10, 9	data input
Q0, Q1, Q2, Q3	3, 2, 6, 7	flip-flop output
\overline{CE}	4	count enable input (active LOW)
$\overline{U/D}$	5	up/down input
GND	8	ground (0 V)
\overline{PL}	11	parallel load input (active LOW)
TC	12	terminal count output
\overline{RC}	13	ripple clock output (active LOW)
CP	14	clock input (LOW-to-HIGH, edge-triggered)
V _{CC}	16	supply voltage







6. Functional description



Table 3. Function table^[1]

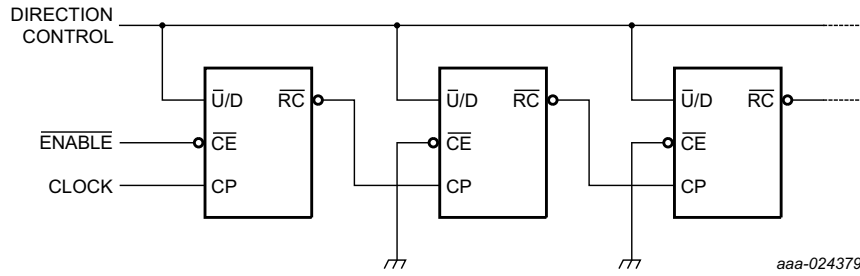
Operating mode	Input					Output
	\overline{PL}	$\overline{U/D}$	\overline{CE}	CP	Dn	Qn
parallel load	L	X	X	X	L	L
	L	X	X	X	H	H
count up	H	L	I	↑	X	count up
count down	H	H	I	↑	X	count down
Hold (do nothing)	H	X	H	X	X	no change

- [1] H = HIGH voltage level
 L = LOW voltage level
 I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition
 X = don't care
 ↑ = LOW-to-HIGH clock transition

Table 4. TC and RC Function table^[1]

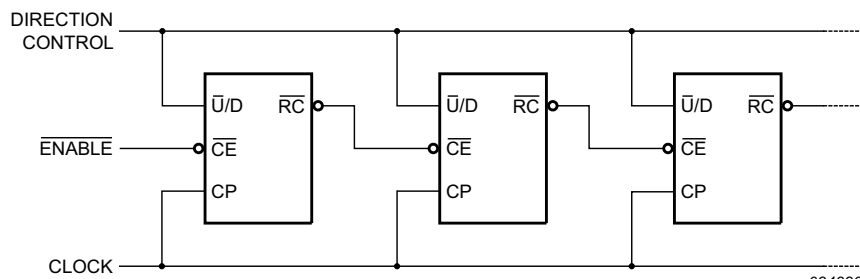
Input			Terminal count state				Output	
$\overline{U/D}$	\overline{CE}	CP	Q0	Q1	Q2	Q3	TC	RC
H	H	X	H	H	H	H	L	H
L	H	X	H	H	H	H	H	H
L	L		H	H	H	H		
L	H	X	L	L	L	L	L	H
H	H	X	L	L	L	L	H	H
H	L		L	L	L	L		

- [1] H = HIGH voltage level
 L = LOW voltage level
 X = don't care
 = one LOW level pulse
 = TC goes LOW on a LOW-to-HIGH clock transition



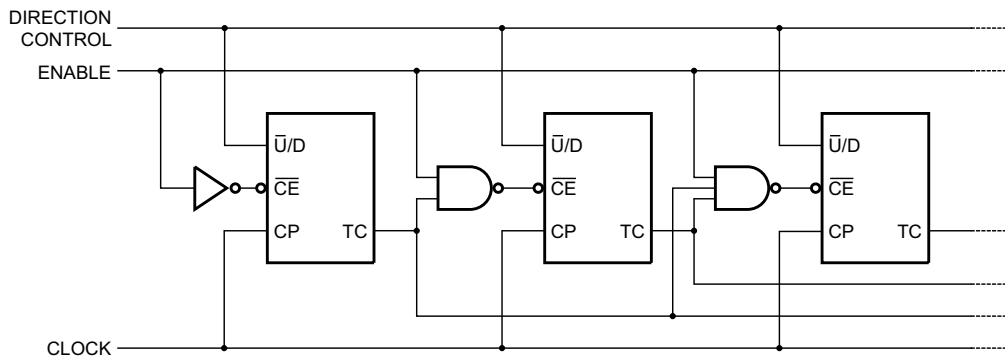
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Fig 5. N-stage ripple counter using ripple clock



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Fig 6. Synchronous n-stage counter using ripple carry/borrow



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Fig 7. Synchronous n-stage counter with parallel gated carry/borrow

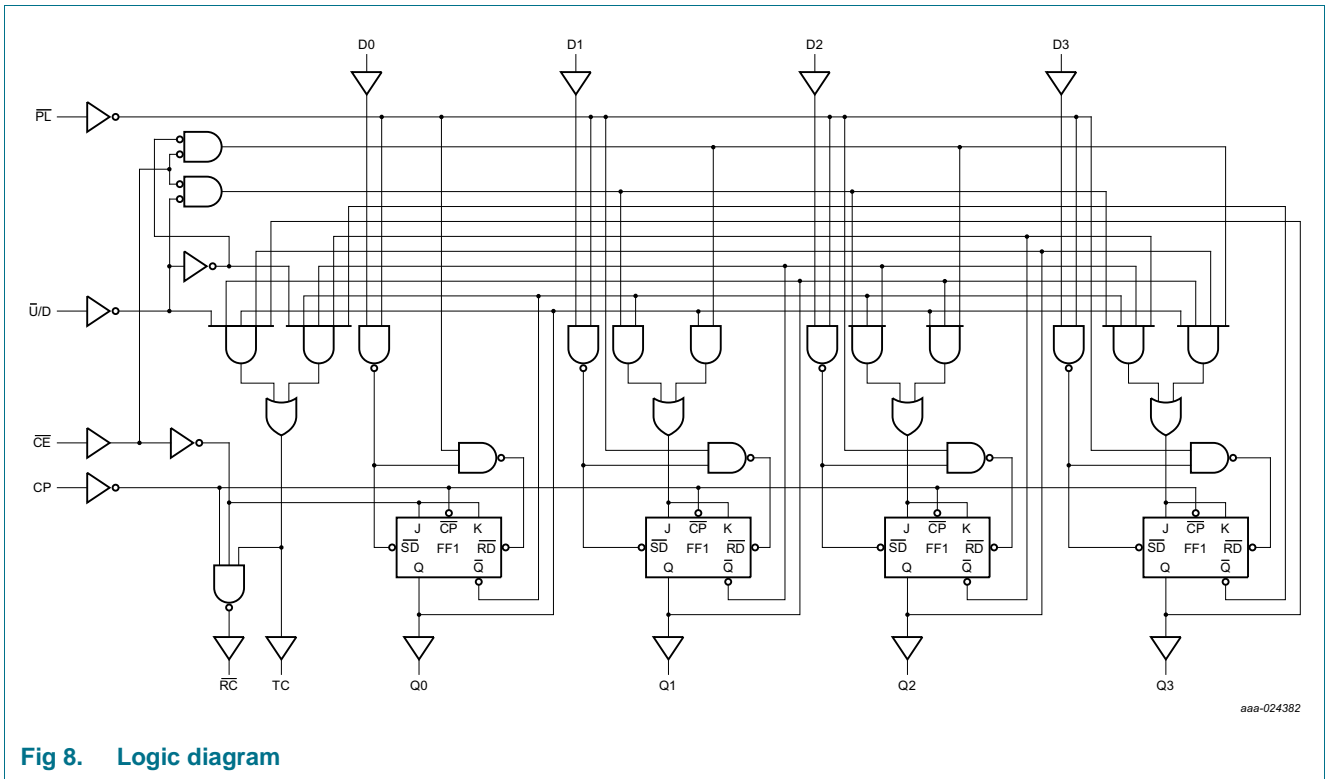


Fig 8. Logic diagram

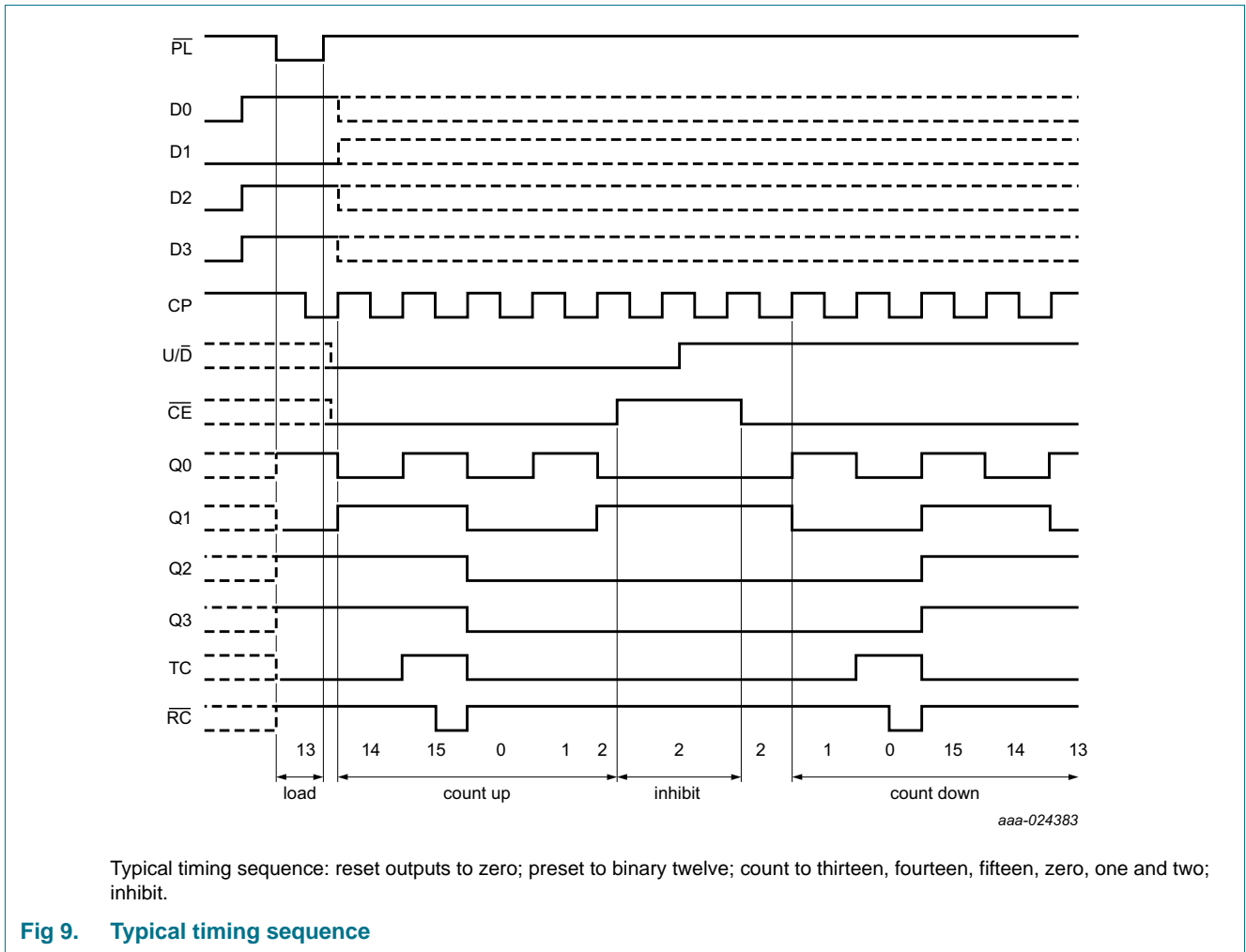


Fig 9. Typical timing sequence

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	SO16 package [1]	-	500	mW
		(T)SSOP16 package [1]	-	500	mW

[1] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.

For (T)SSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

8. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		2.0	5.0	6.0	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	ns/V
		V _{CC} = 4.5 V	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	ns/V

9. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -4.0; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = -5.2; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80.0	-	160.0	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 18](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{pd}	propagation delay	CP to Qn; see Figure 10 ^[1]								
		$V_{CC} = 2.0$ V	-	72	220	-	275	-	330	ns
		$V_{CC} = 4.5$ V	-	26	44	-	55	-	66	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	22	-	-	-	-	-	ns
		$V_{CC} = 6.0$ V	-	21	37	-	47	-	56	ns
		CP to TC; see Figure 10								
		$V_{CC} = 2.0$ V	-	83	255	-	320	-	395	ns
		$V_{CC} = 4.5$ V	-	30	51	-	64	-	77	ns
		$V_{CC} = 6.0$ V	-	24	43	-	54	-	65	ns
		CP to \overline{RC} ; see Figure 11								
		$V_{CC} = 2.0$ V	-	47	150	-	190	-	225	ns
		$V_{CC} = 4.5$ V	-	17	30	-	38	-	45	ns
		$V_{CC} = 6.0$ V	-	14	26	-	33	-	38	ns
		\overline{CE} to \overline{RC} ; see Figure 11								
		$V_{CC} = 2.0$ V	-	33	130	-	165	-	195	ns
		$V_{CC} = 4.5$ V	-	12	26	-	33	-	39	ns
		$V_{CC} = 6.0$ V	-	10	22	-	28	-	33	ns
		Dn to Qn; see Figure 12								
		$V_{CC} = 2.0$ V	-	61	220	-	275	-	330	ns
		$V_{CC} = 4.5$ V	-	22	44	-	55	-	66	ns
		$V_{CC} = 6.0$ V	-	18	37	-	47	-	56	ns
		PL to Qn; see Figure 13								
		$V_{CC} = 2.0$ V	-	61	220	-	275	-	330	ns
		$V_{CC} = 4.5$ V	-	22	44	-	55	-	66	ns
$V_{CC} = 6.0$ V	-	18	37	-	47	-	56	ns		
U/D to TC; see Figure 14										
$V_{CC} = 2.0$ V	-	44	190	-	240	-	285	ns		
$V_{CC} = 4.5$ V	-	16	38	-	48	-	57	ns		
$V_{CC} = 6.0$ V	-	13	32	-	41	-	48	ns		
U/D to \overline{RC} ; see Figure 14										
$V_{CC} = 2.0$ V	-	50	210	-	265	-	315	ns		
$V_{CC} = 4.5$ V	-	18	42	-	53	-	63	ns		
$V_{CC} = 6.0$ V	-	14	36	-	45	-	54	ns		
t_t	transition time	see Figure 15 ^[2]								
		$V_{CC} = 2.0$ V	-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5$ V	-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0$ V	-	6	13	-	16	-	19	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 18](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_w	pulse width	CP; HIGH or LOW; see Figure 10								
		$V_{CC} = 2.0$ V	125	28	-	155	-	195	-	ns
		$V_{CC} = 4.5$ V	25	10	-	31	-	39	-	ns
		$V_{CC} = 6.0$ V	21	8	-	26	-	33	-	ns
		\overline{PL} ; LOW; see Figure 15								
		$V_{CC} = 2.0$ V	100	22	-	125	-	150	-	ns
		$V_{CC} = 4.5$ V	20	8	-	25	-	30	-	ns
	$V_{CC} = 6.0$ V	17	6	-	21	-	26	-	ns	
t_{rec}	recovery time	\overline{PL} to CP; see Figure 15								
		$V_{CC} = 2.0$ V	35	8	-	45	-	55	-	ns
		$V_{CC} = 4.5$ V	7	3	-	9	-	11	-	ns
		$V_{CC} = 6.0$ V	6	2	-	8	-	9	-	ns
t_{su}	set-up time	$\overline{U/D}$ to CP; see Figure 17								
		$V_{CC} = 2.0$ V	205	50	-	255	-	310	-	ns
		$V_{CC} = 4.5$ V	41	18	-	51	-	62	-	ns
		$V_{CC} = 6.0$ V	35	14	-	43	-	53	-	ns
		Dn to \overline{PL} ; see Figure 16								
		$V_{CC} = 2.0$ V	100	19	-	125	-	150	-	ns
		$V_{CC} = 4.5$ V	20	7	-	25	-	30	-	ns
		$V_{CC} = 6.0$ V	17	6	-	21	-	26	-	ns
		\overline{CE} to CP; see Figure 17								
		$V_{CC} = 2.0$ V	140	44	-	175	-	210	-	ns
		$V_{CC} = 4.5$ V	28	16	-	35	-	42	-	ns
		$V_{CC} = 6.0$ V	24	13	-	30	-	36	-	ns
t_h	hold time	$\overline{U/D}$ to CP; see Figure 17								
		$V_{CC} = 2.0$ V	0	-39	-	0	-	0	-	ns
		$V_{CC} = 4.5$ V	0	-14	-	0	-	0	-	ns
		$V_{CC} = 6.0$ V	0	-11	-	0	-	0	-	ns
		Dn to \overline{PL} ; see Figure 16								
		$V_{CC} = 2.0$ V	0	-11	-	0	-	0	-	ns
		$V_{CC} = 4.5$ V	0	-4	-	0	-	0	-	ns
		$V_{CC} = 6.0$ V	0	-3	-	0	-	0	-	ns
		\overline{CE} to CP; see Figure 17								
		$V_{CC} = 2.0$ V	0	-28	-	0	-	0	-	ns
		$V_{CC} = 4.5$ V	0	-10	-	0	-	0	-	ns
		$V_{CC} = 6.0$ V	0	-8	-	0	-	0	-	ns

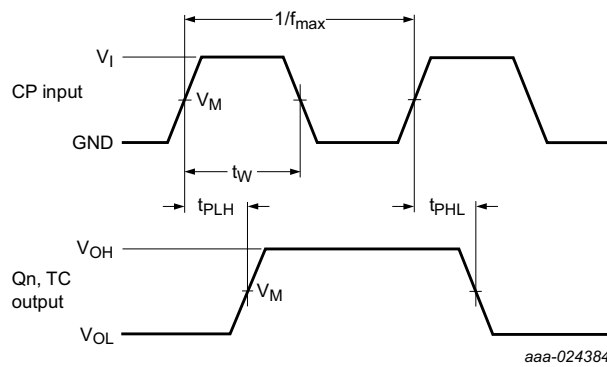
Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see [Figure 18](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
f_{max}	maximum frequency	CP; see Figure 10								
		$V_{\text{CC}} = 2.0 \text{ V}$	4.0	11	-	3.2	-	2.6	-	MHz
		$V_{\text{CC}} = 4.5 \text{ V}$	20	33	-	16	-	13	-	MHz
		$V_{\text{CC}} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	36	-	-	-	-	-	MHz
	$V_{\text{CC}} = 6.0 \text{ V}$	24	39	-	19	-	15	-	MHz	
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{\text{CC}}; V_{\text{CC}} = 5 \text{ V}; f_i = 1 \text{ MHz}$ [3]	-	31	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
 $P_D = C_{\text{PD}} \times V_{\text{CC}}^2 \times f_i \times N + \sum(C_L \times V_{\text{CC}}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{\text{CC}}^2 \times f_o)$ = sum of outputs.

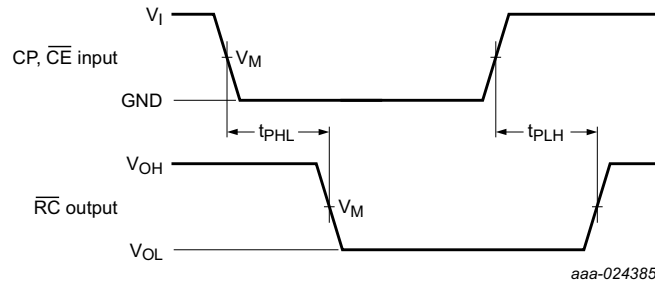
11. Waveforms



Measurement points are given in [Table 9](#).

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

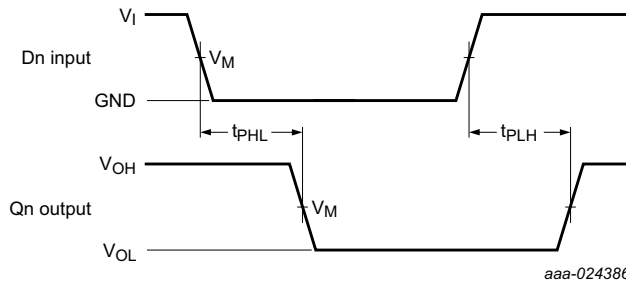
Fig 10. The clock input (CP) to outputs (Qn, TC) propagation delays, clock pulse width and maximum clock frequency



Measurement points are given in [Table 9](#).

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

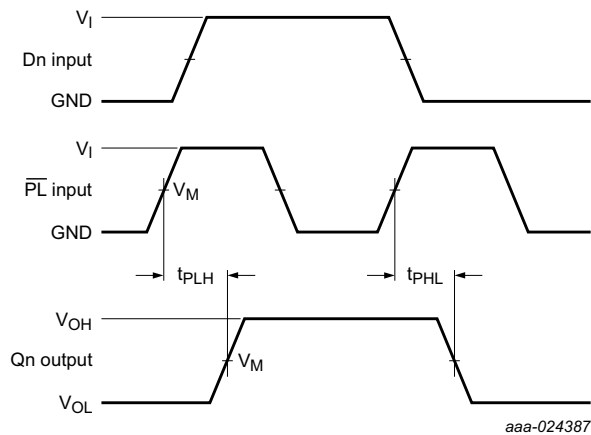
Fig 11. The clock and count enable inputs (CP, CE) to ripple clock output (RC) propagation delays



Measurement points are given in [Table 9](#).

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

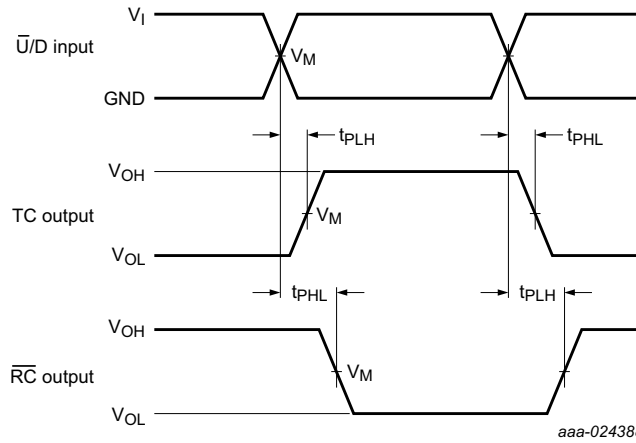
Fig 12. The input (Dn) to output (Qn) propagation delays



Measurement points are given in [Table 9](#).

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

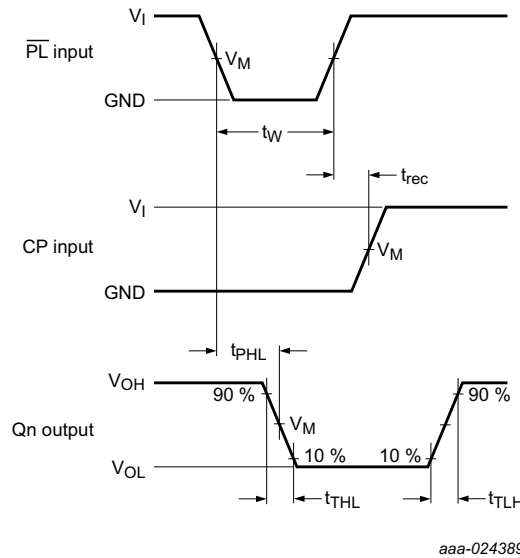
Fig 13. The parallel load input (PL) to output (Qn) propagation delays



Measurement points are given in [Table 9](#).

Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

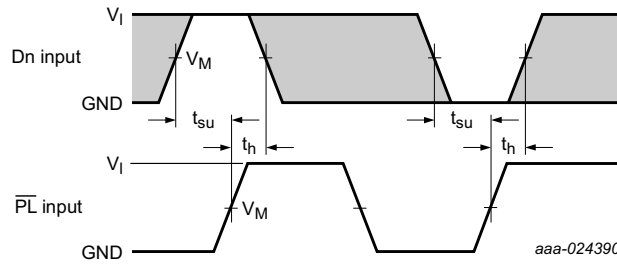
Fig 14. The up/down count input (\bar{U}/D) to terminal count and ripple clock output (TC, \overline{RC}) propagation delays



Measurement points are given in [Table 9](#).

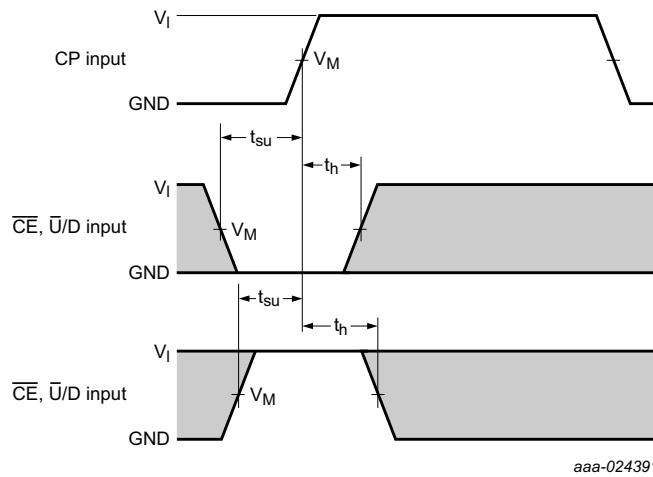
Logic levels V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 15. The parallel load input (\overline{PL}) to clock (CP) recovery times, parallel load pulse width and output (Q_n) transition times



The shaded areas indicate when the input is permitted to change for predictable output performance. Measurement points are given in [Table 9](#).

Fig 16. The parallel load input (\overline{PL}) to data input (Dn) set-up and hold times

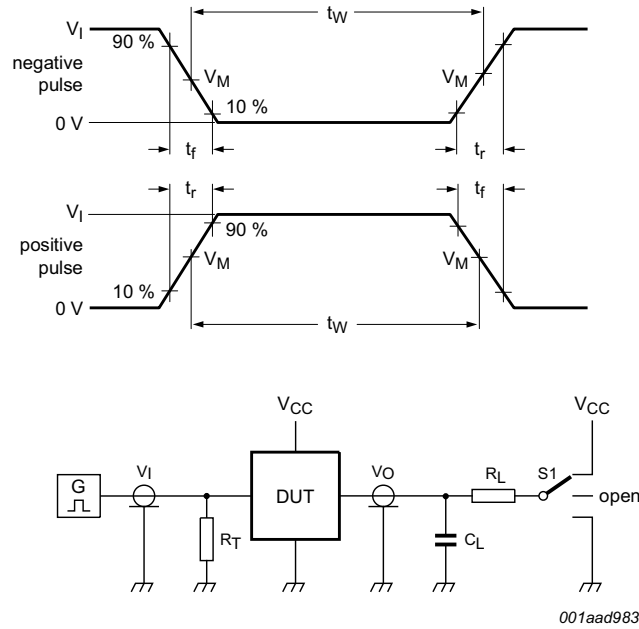


The shaded areas indicate when the input is permitted to change for predictable output performance. Measurement points are given in [Table 9](#).

Fig 17. The count enable and up/down count inputs (\overline{CE} , $\overline{U/D}$) to clock input (CP) set-up and hold times

Table 9. Measurement points

Input		Output
V_M	V_I	V_M
$0.5 \times V_{CC}$	GND to V_{CC}	$0.5 \times V_{CC}$



001aad983

Test data is given in [Table 10](#).

Test circuit definitions:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistance.

$S1$ = Test selection switch

Fig 18. Test circuit for measuring switching times

Table 10. Test data

Input		Load		S1 position
V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

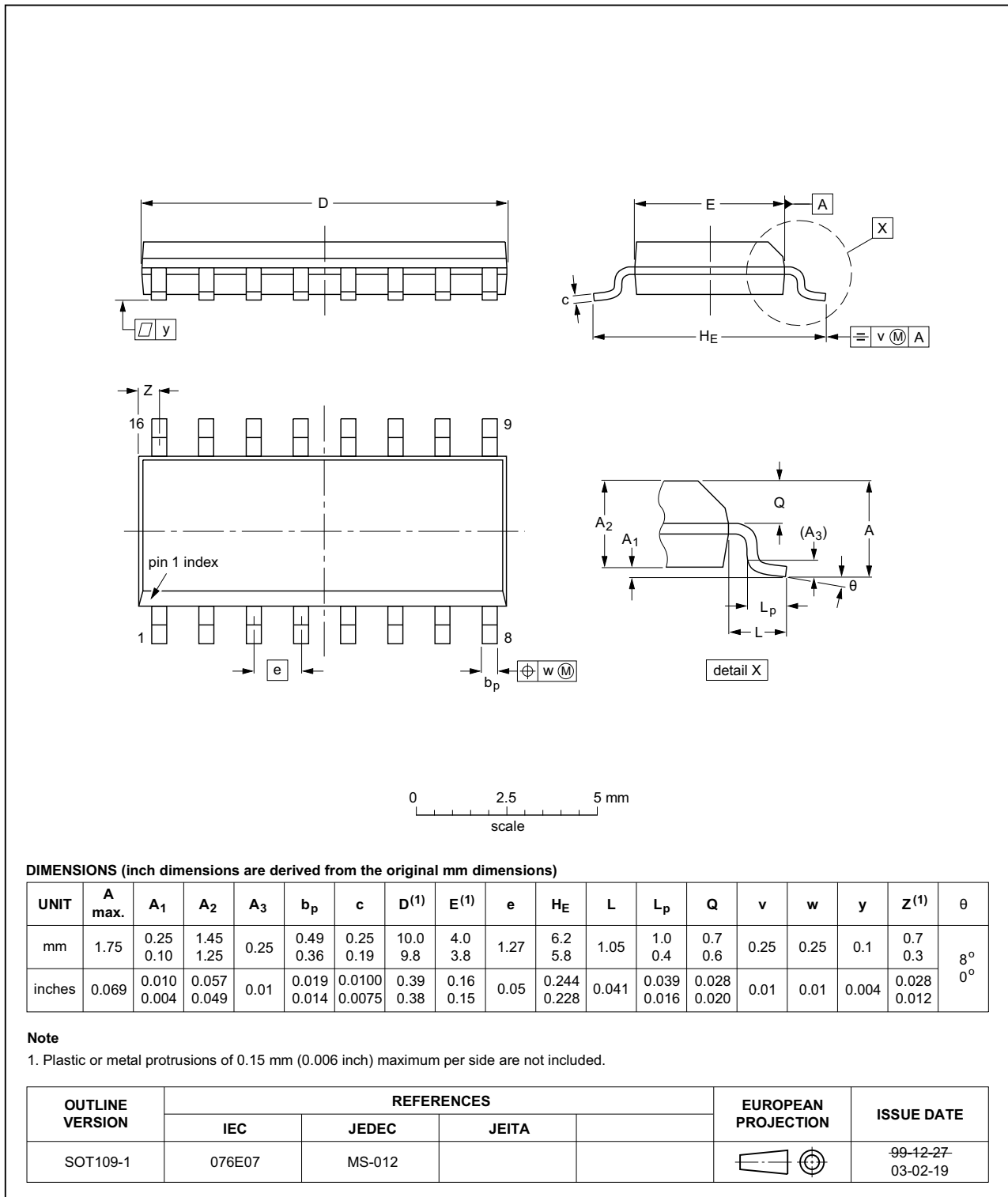


Fig 19. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

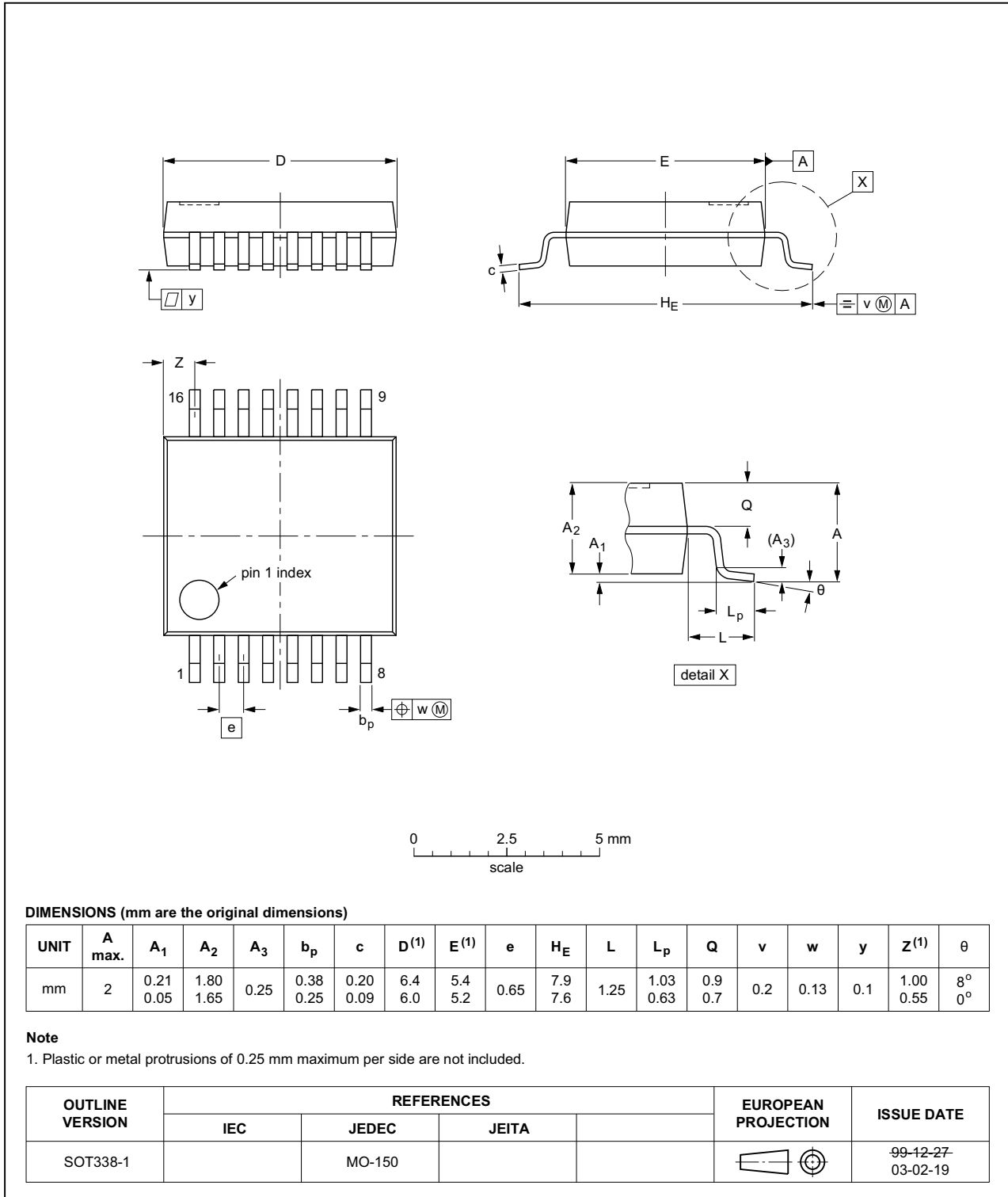


Fig 20. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

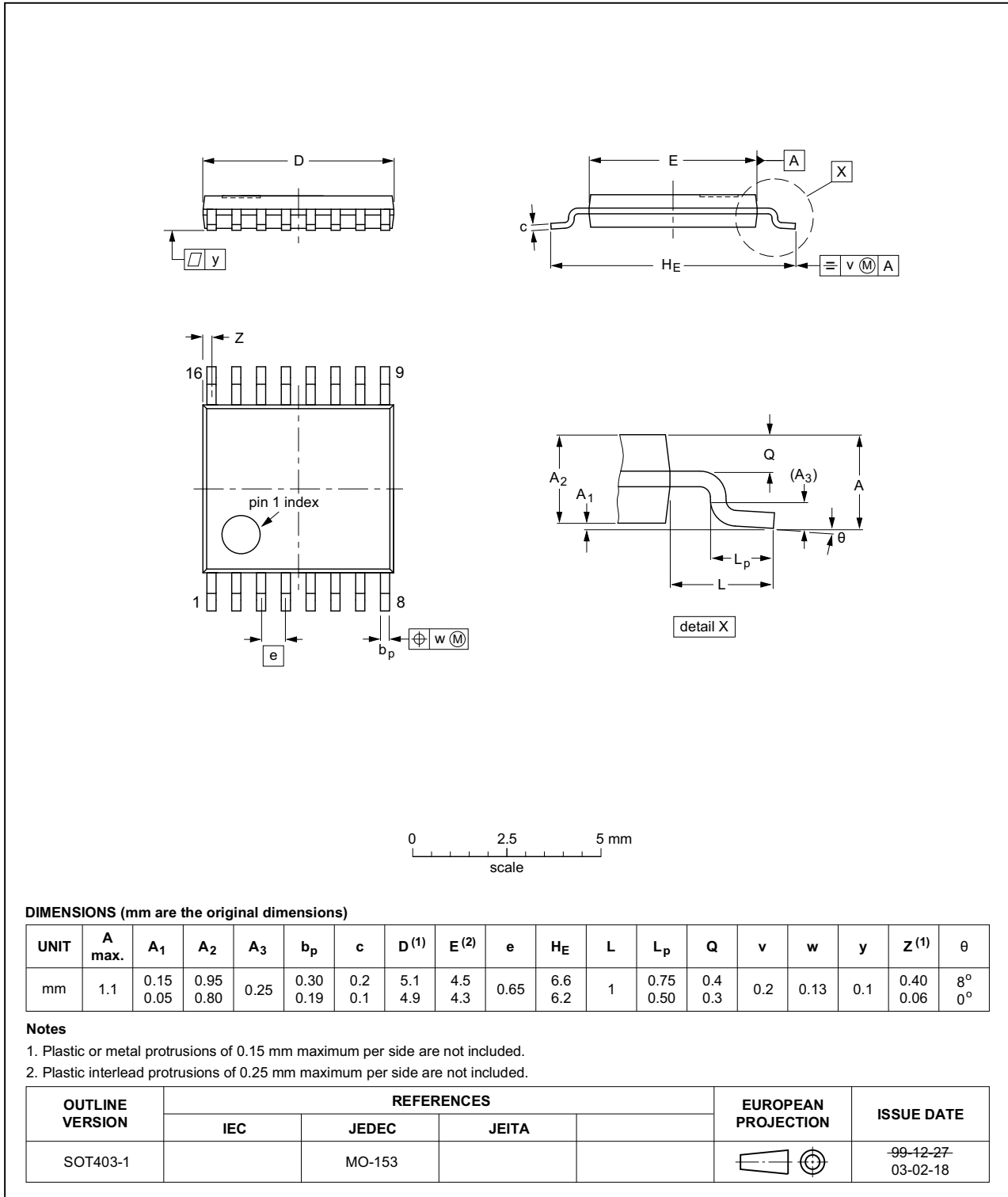


Fig 21. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC191 v.3	20170103	Product data sheet	-	74HC_HCT191 v.2
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Type numbers 74HCT191D, 74HCT191DB, 74HCT191PW removed. 			
74HC_HCT191_CNV v.2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 3 January 2017

Document identifier: 74HC191